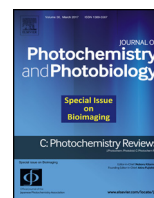




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Review

Photochemistry and photo-electrochemistry on synthetic semiconducting diamond

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ABSTRACT

In this short review, we discuss the photo-relative properties, photochemical and photo-electrochemical applications of synthetic diamond materials. Synthetic diamond with semiconductive nature owns outstanding ideal properties of physics and chemistry, including high hardness, a wide bandgap, very high carrier mobility, excellent chemical stability, and inherent biocompatibility, which makes diamond promising candidate used in photochemistry and photo-electrochemistry. Diamond materials show p-type or n-type properties via doping of certain elements, which can be utilized in photo-involved chemistry for photo-synthesis, photo-catalysis, solar cells, photo-electronics, and surface modification.

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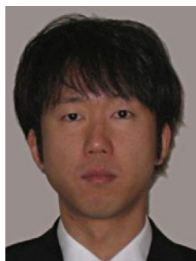
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1. Introduction

1.1. Synthetic diamond materials

Diamond materials, including the synthetic ones, are attracted attentions in various scientific and engineering fields due to their chemical stability and high hardness [1,2]. Owing to the outstanding electronic and electrochemical properties of diamond, progress has been made on applying diamond in fields like environmental protection, health care and biochemical applications [3–6]. Hydrogen-terminated diamond is an excellent kind of sensing material used in electrochemical and biological sensor devices. Most diamond systems involving photochemical and photo-electrochemical reactions do not require gem-quality diamonds, but rather millions of microscopic diamond crystals. The usage of diamond materials is an ideal solution to the problem rising from the degradation of interfaces of many traditional materials used in microelectronic devices (e.g. glass, silicon, and gold). Synthetic diamond materials, mainly as thin films and particles, have been especially attractive in the development of integrated sensors and devices because of good electrical, chemical, and biocompatible properties [7–9]. Photochemical and photo-electrochemical investigations on diamond would be helpful for deeply understanding of

Table 1

The band gap and work function of carbon materials (Ref. [23]).

	Bandgap (eV)	Work function (eV)
Amorphous carbon	0.2–3.0	4.9
Diamond	5.5	5.45
Graphite	0	5.0
Fullerene (C ₆₀)	1.6	4.6–5.0
Carbon nanotubes (CNT)	0.3–2.0	4.5–5.1
Graphene	0–0.3	5.0

diamond-electrolyte systems, their photo activities, and diamond semiconductive properties.

The mainstream of synthetic diamond materials used in the photochemical and photo-electrochemical applications is semiconductive diamond films. Researchers now can prepare polycrystalline diamond through chemical vapor deposition (CVD) technology. To expand its application in photo-electrochemical field, preparation of Boron-doped diamond (BDD) thin films have been developed. As an ideal platform for optical, electrochemical, mechanic and electronic applications, BDD materials have excellent advantages including chemical robustness, wide electrochemical potential window, resistance to corrosion, low background current, optical transparency and biocompatibility [10,11], which make them the most popular diamond materials used in photochemical and photo-electrochemical applications. BDD thin layers can be deposited on quartz, glass, and polymer with optical transparency (about 300–1000 nm range) [13–15], which varies from ultrananocrystalline, through nanocrystalline, and polycrystalline to single crystal materials. When illuminated with light of certain wavelength and in an electrical field from outside, the photo-generated charge carriers in BDD films are accelerated and flow through the grain boundaries, generating an electron current that shows a diode-like behavior.

In addition, diamond nanoparticle (NDs, including diamond powder) and amorphous diamond (or diamond-like carbon, DLC) are sometimes employed in photo-involved applications. NDs are prepared by explosive method for the detonation of carbon materials. NDs materials with small size (normally 4–5 nm) have high specific surface areas, on which a large number of reactive chemical groups are located [16–19]. Amorphous diamond (or DLC), with tetrahedral carbon structures containing no non-carbon impurities and mixture with distorted sp² and sp³ bonds, is also an excellent choice used in photo-electronic devices [20–22].

1.2. Diamond semiconducting property

The electrochemical and photo-electrochemical behavior of diamond materials have been studied in relation to their semiconducting characteristics. All the stable carbon allotropes, with a number of properties in photovoltaic industry, are listed in Table 1 [23,24]. They can work as insulators or semiconductors in the manner of diamond or diamond-like carbon, metallic and semi-metallic in the case of graphite or graphene, or conducting and semiconducting in the case of fullerene and carbon nanotubes [25].

Nowadays thin diamond films, which are widely used in laboratories and industry, can be prepared by CVD methods [9]. Until now tremendous progress has been made in the CVD technology for preparation of diamond materials on large-area silicon, Mo, quartz, glass, etc [9,13]. It was shown that synthetic polycrystalline diamond films by CVD devices, with different growth conditions, show a wide varieties of physical properties [26,27]. The differences include the layer thickness, grain size, surface roughness, and atom clusters. By doping of other elements, active impurities could be introduced into diamond showing p- or n-type conductivity, which is necessary for the applications in semiconductor devices [28]. By boron doping, p-type semiconducting (using holes as the

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